

ABSTRACT

The present invention is a method for producing a wafer comprising, at least, a BMD forming step of subjecting a silicon single crystal in a state of an ingot to heat treatment thereby to form bulk micro defects (BMDs) inside, and a wafer processing step of processing the ingot in which the bulk micro defects (BMDs) was formed into wafers. Thereby, there can be provided a method for producing a wafer, wherein heat treatment for providing IG capability in production of wafer can be shortened and wafers with high IG capability can be produced in large quantity. Also, the present invention can further comprise a wafer heat-treating step of subjecting the processed wafer to heat treatment, or an epitaxial growth step of forming an epitaxial layer on the wafer. Thereby, there is improved productivity of annealed wafers or epitaxial wafers that are excellent in gettering capability.